

H3S065E040

Part Number	Package	Marking
H3S065E040	TO-247-3L	H3S065E040

Product Summary

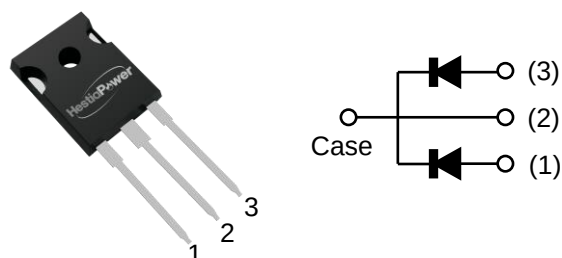
V_R	650V
$I_{F(135/157^{\circ}C)}$	67A/40A**
Q_C	110nC**



Features

- Low Conduction and Switching Loss
- Zero Reverse Recovery
- Temperature Independent Switching Behavior
- Positive Temperature Coefficient Device
- High Surge Current Capability
- RoHS Compliant and Halogen Free
- Suitable for High Speed Application
- AEC-Q101 Qualified

Circuit Diagram



Benefits

- Higher System Efficiency
- Increase Parallel Device Convenience
- Enable High Temperature Application
- Allow High Frequency Operation
- Realize Compact and Lightweight Systems
- High Reliability

Applications

- Switching Mode Power Supply
- PFC
- UPS
- Motor Drives
- Flywheel diode in Power Inverters
- Solar/Wind Renewable Energy

Absolute Maximum Ratings ($T_C = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	$T_J = 25^{\circ}C$	650	V
Peak Reverse Surge Voltage	V_{RSM}	$T_J = 25^{\circ}C$	650	V
DC Blocking Voltage	V_R	$T_J = 25^{\circ}C$	650	V
Continuous Forward Current (Per Leg/Per Device)	I_F	$T_C = 25^{\circ}C$	72.5*/145**	A
		$T_C = 135^{\circ}C$	33.5*/67**	
		$T_C = 157^{\circ}C$	20*/40**	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	$T_C = 25^{\circ}C, T_P = 10 \text{ ms, Half Sine Wave}$	150*/***	A
		$T_C = 125^{\circ}C, T_P = 10 \text{ ms, Half Sine Wave}$	136*/***	
		$T_C = 25^{\circ}C, T_P = 10 \mu s, \text{ Pulse}$	1854*/***	
Repetitive Peak Forward Surge Current	I_{FRM}	$T_C = 25^{\circ}C, T_P = 10 \text{ ms}$ Half Sine Wave, $D = 0.1$	128*/***	A
		$T_C = 125^{\circ}C, T_P = 10 \text{ ms}$ Half Sine Wave, $D = 0.1$	105*/***	
Power Dissipation	P_D	$T_C = 25^{\circ}C$	263*	W
		$T_C = 125^{\circ}C$	87*	
I^2t value	$\int i^2 dt$	$T_C = 25^{\circ}C, T_P = 10 \text{ ms}$	112*/***	A^2s
Junction & Storage Temperature	T_J, T_{stg}		-55 to 175	$^{\circ}C$
Soldering Temperature	T_L		260	
Mounting Torque	M_D	M3 or 6-32 screw	1.0	Nm

*Per Leg **Whole Device ***Estimation

Electrical Characteristics (Per Leg) ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
DC Blocking Voltage	V_{DC}	$I_R = 100\ \mu\text{A}$, $T_J = 25^\circ\text{C}$	> 650			V
Forward Voltage	V_F	$I_F = 20\text{A}$, $T_J = 25^\circ\text{C}$		1.4	1.7	V
		$I_F = 20\text{A}$, $T_J = 175^\circ\text{C}$		1.55	1.9	V
Reverse Current	I_R	$V_R = 650\text{V}$, $T_J = 25^\circ\text{C}$		3	150	μA
		$V_R = 650\text{V}$, $T_J = 175^\circ\text{C}$		40	600	μA
Total Capacitive Charge	Q_C	$I_F = 20\text{A}$, $dI/dt = 300\text{A}/\mu\text{s}$ $V_R = 400\text{V}$, $T_J = 25^\circ\text{C}$		55		nC
Total Capacitance	C_j	$V_R = 0.1\text{V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$		1544		pF
		$V_R = 200\text{V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$		134		
		$V_R = 400\text{V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$		104		
Capacitance Stored Energy	E_C	$V_R = 400\text{V}$		11		μJ

Thermal Resistance (Per Leg)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		0.57		$^\circ\text{C}/\text{W}$

Naming Rule

H3 S 065 E 040

Generation

H3 = 3rd Gen Discrete

Device Type

S = JBS diode (High Power) D = JBS diode (High Speed)

Breakdown Voltage

065 = 650V 120 = 1200V 170 = 1700V

Package

E = TO-247-3L (Dual)

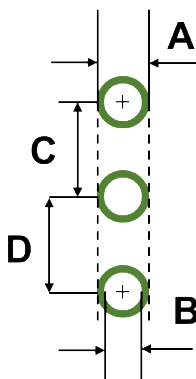
Typical Current Rating

012 = 12A 016 = 16A 020 = 20A 030 = 30A 040 = 40A

Recommended Solder Pad Layout

TO-247-3L

Parameter	Symbol	Typical	Unit
Length	A	3.048	mm
	B	2.032	
	C	5.436	
	D	5.436	



Typical Device Performance (Per Leg)

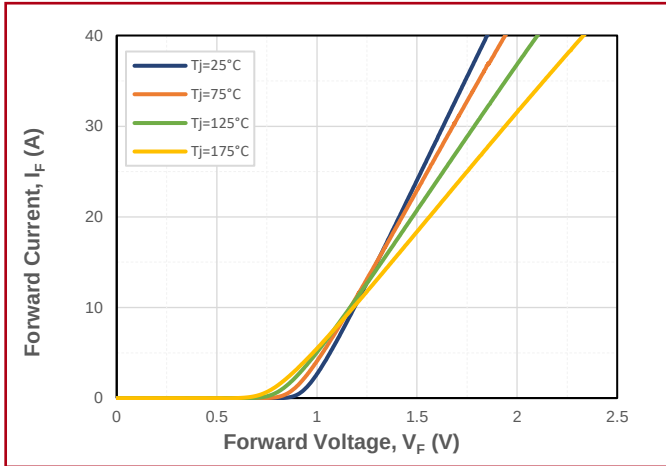


Fig.1 Forward Characteristics

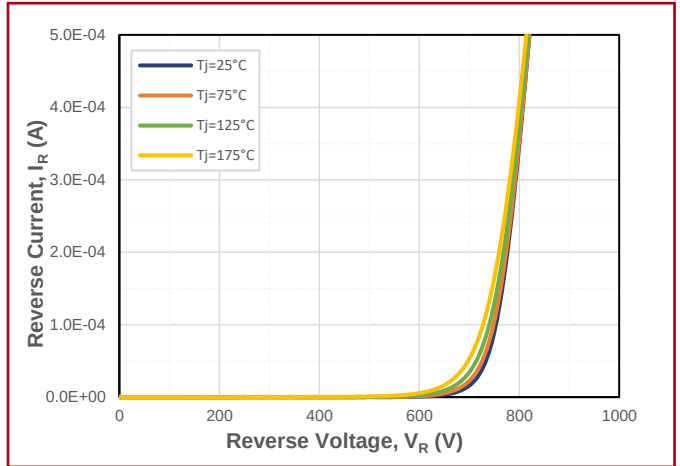


Fig.2 Reverse Characteristics

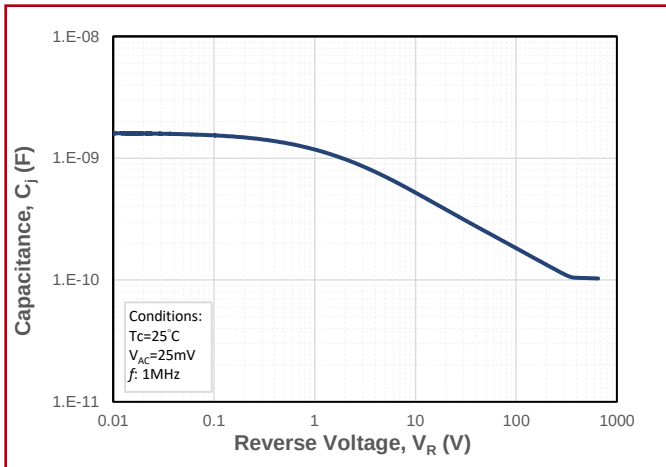


Fig.3 Junction Capacitance vs. Reverse Voltage

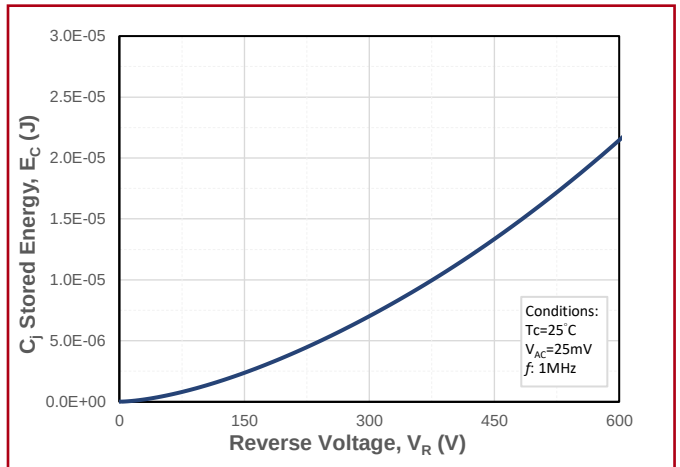


Fig.4 Capacitance Stored Energy

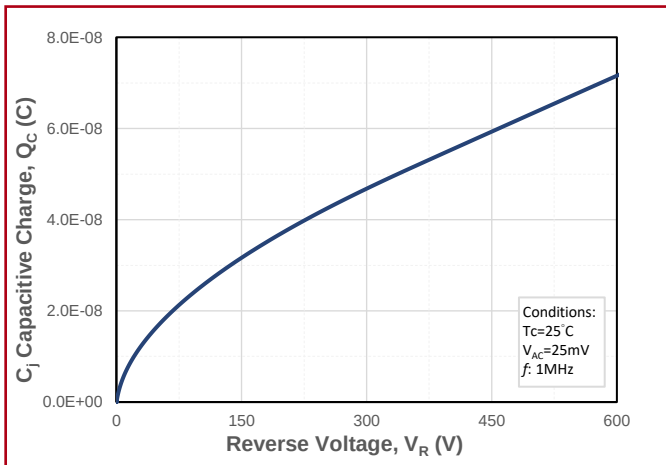


Fig.5 Recovery Charge vs. Reverse Voltage

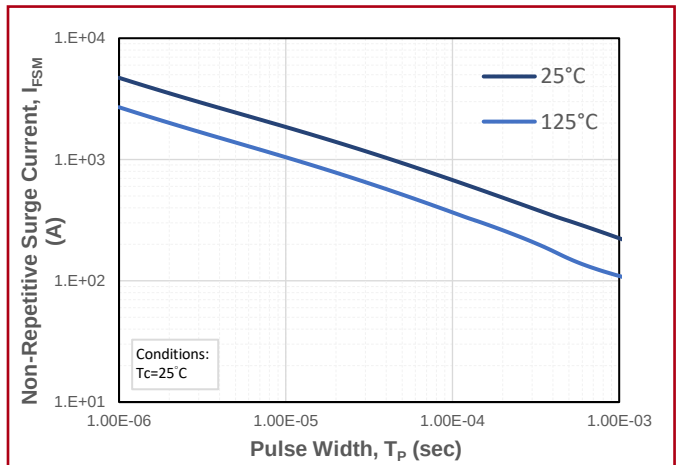


Fig.6 Non-Repetitive Peak Forward Surge Current (Pulse Mode)

Typical Device Performance (Per Leg)

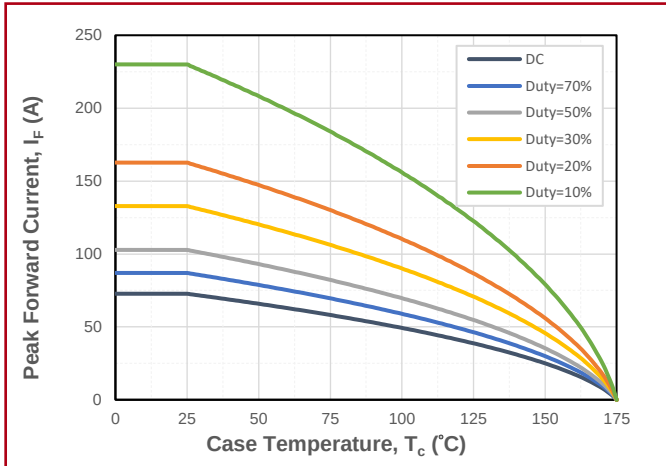


Fig.7 Maximum Forward Current Derating vs. Case Temperature

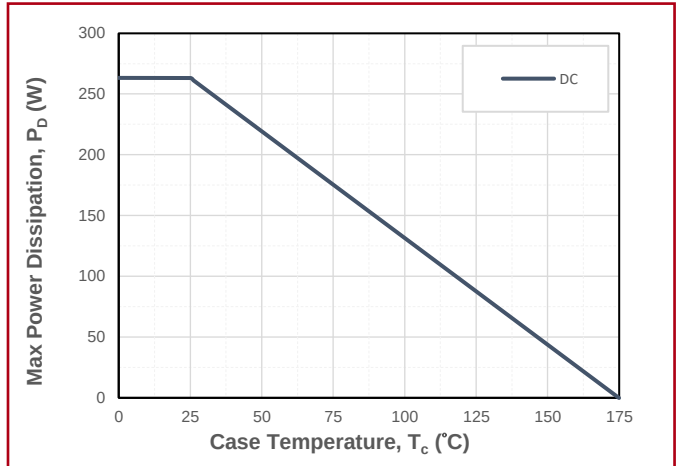


Fig.8 Maximum Power Dissipation Derating vs. Case Temperature

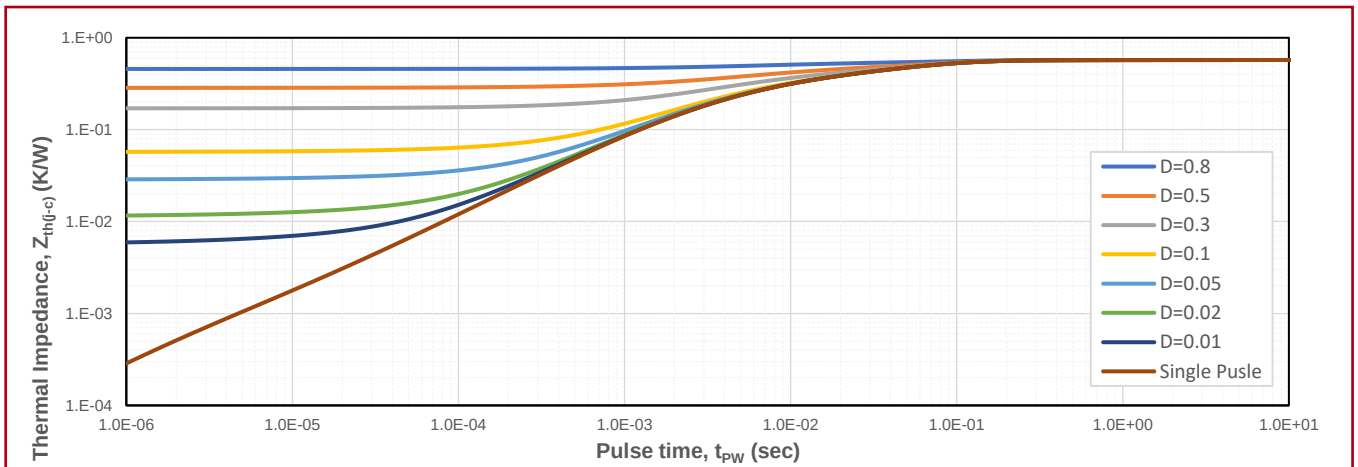
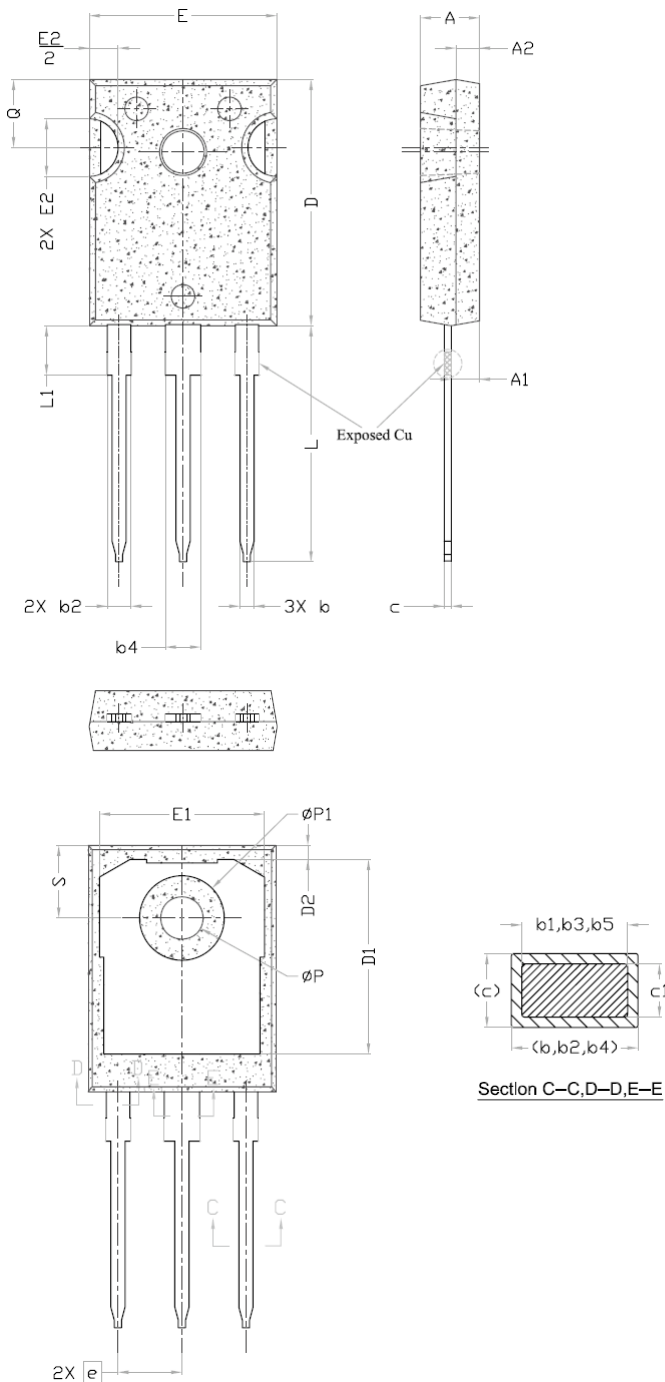


Fig.9 Transient Junction to Case Thermal Impedance

The information provided herein is subject to change without notice.

Package Dimensions (TO-247-3L)



SYMBOL	DIMENSIONS			Note
	Min.	Typ.	Max.	
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.50	2.00	2.49	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.55	0.60	0.69	6
c1	0.55	0.60	0.65	
D	20.80	20.95	21.10	4
D1	16.25	16.55	17.65	5
D2	0.51	1.19	1.35	
E	15.75	15.94	16.13	4
E1	13.46	14.02	14.16	5
E2	4.32	4.91	5.49	3
e	5.44 BSC			
L	19.81	20.07	20.32	
L1	4.10	4.19	4.40	6
ϕP	3.56	3.61	3.65	7
$\phi P1$	7.19 REF.			
Q	5.39	5.79	6.20	
S	6.04	6.17	6.30	

Note:

- Package Reference: JEDEC TO247, Variation AD.
- All Dimensions Are In mm.
- Slot Required, Notch May Be Rounded
- Dimension D & E Do Not Include Mold Flash. Mold Flash Shall Not Exceed 0.127mm Pre Side. These Dimensions Are Measured At The Outermost Extreme Of The Plastic Body.
- Thermal Pad Contour Optional Within Dimension D1 & E1.
- Lead Finish Uncontrolled In L1.
- ϕP To Have A Maximum Draft Angle Of 1.5° To The Top Of The Part With A Maximum Hole Diameter Of 3.91mm.
- Dimension "b2" And "b4" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.10mm Total In Excess Of "b2" And "b4" Dimension At Maximum Material Condition.

Notes

- The information provided herein is subject to change without notice.
- For other information that does not show on this datasheet, please contact us for inquiry.